ROHM

Specification	Products	Type BCW71

1. SCOPE BCW71

1.1 Scope. This specification covers the detail requirements for one type NPN silicon epitaxial planar transistor designed for audio frequency small signal amplifier.

1.2 Physical dimensions. See figure 1.

1.3 Absolute maximun ratings. (Ta=25 ℃)

Collector to base voltage	V_{CBO}	50V
Collector to emitter voltage	V_{CEO}	45V
Emitter to base voltage	V_{EBO}	5V
Collector current	I_C	100mA
Power dissipation-Free Air	P_C	200mW
*Power dissipation-Ceramic Substrate	P_C	350mW
Junction temperature	Tj	150℃
Storage temperature range	Tstg	−65～150℃

*Package mounted on ceramic 7×5×0.6mm

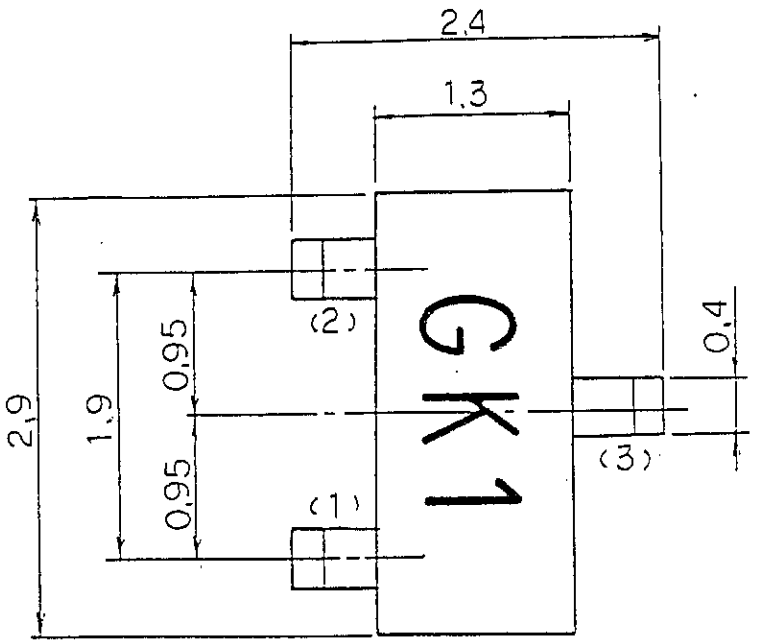
2. Electrical characteristics (Ta=25 ℃)

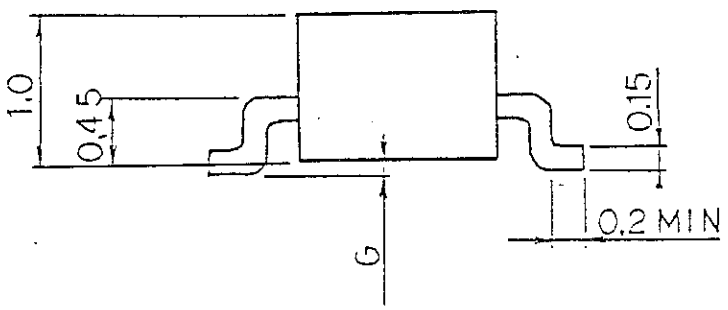
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCBO	IC=50uA	50	—	—	V
BVCEO	IC=2mA	45	—	—	V
BVEBO	IE=50uA	5	—	—	V
ICBO	VCB=20V	—	—	100	nA
VCE(sat)	IC=10mA, IB=0.5mA	—	—	0.25	V
VBE(ON)	VCE=5V, IC=2mA	0.55	—	0.7	V
hFE	VCE=5V, IC=2mA	110	—	230	
Cob	VCB=10V, f=1MHz	—	—	4	pF
NF	VCE=5V, IC=0.2mA, f=1KHz Rs=2kΩ	—	—	10	dB
ICBO	VCB=20V, Ta=100℃	—	—	10	uA

MASTER

ROHM

Specification	Products	Type
		BCW71





UNIT : mm

Low Profil G=0~0.1

High Profil G=0.1~0.25

(1) Emitter
(2) Base
(3) Collector

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